



P-Channel 1.8 V (G-S) MOSFET

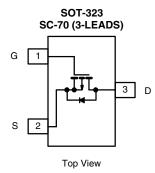
PRODUCT SUMMARY				
V _{DS} (V)	$R_{DS(on)}\left(\Omega\right)$	I _D (A)		
- 8	0.280 at V _{GS} = - 4.5 V	- 0.92		
	0.380 at V _{GS} = - 2.5 V	- 0.79		
	0.530 at V _{GS} = - 1.8 V	- 0.67		

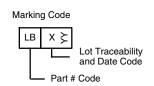
FEATURES

- TrenchFET® Power MOSFET: 1.8 V
- Material categorization: For definitions of compliance please see www.vishav.com/doc?99912



HALOGEN FREE





Ordering Information: Si1305DL-T1-GE3 (Lead (Pb)-free and Halogen-free)

ABSOLUTE MAXIMUM RATINGS	$(T_A = 25 ^{\circ}C, unlet)$	ess otherwise	noted)		
Parameter		Symbol	5 s	Steady State	Unit
Drain-Source Voltage		V _{DS}	- 8		V
Gate-Source Voltage		V _{GS}	± 8		
Outilities Durin Outub (T., 450,00)	T _A = 25 °C	- I _D	- 0.92	- 0.86	^
Continuous Drain Current (T _J = 150 °C) ^a	T _A = 70 °C		- 0.74	- 0.69	
Pulsed Drain Current		I _{DM}	- 3		Α
Continuous Diode Current (Diode Conduction) ^a		I _S	- 0,28	- 0.24	
Maximum Power Dissipation ^a	T _A = 25 °C	- P _D	0.34	0.29	W
	T _A = 70 °C		0.22	0.19	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150		°C

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Manipulation to Application	t ≤ 5 s	R _{thJA}	315	375	°C/W
Maximum Junction-to-Ambient ^a	Steady State		360	430	
Maximum Junction-to-Foot (Drain)	Steady State	R _{thJF}	285	340	

Note:

a. Surface mounted on 1" x 1" FR4 board.

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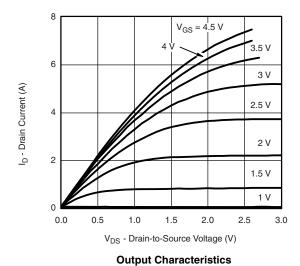
SPECIFICATIONS (T _J = 25 °C, unless otherwise noted)								
Parameter	Symbol	Test Conditions	Min. Typ.		Max.	Unit		
Static								
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}$, $I_D = -250 \mu A$	- 0.45			V		
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 8 \text{ V}$			± 100	nA		
Zana Oata Walkana Busin Oursell	I _{DSS}	V _{DS} = -8 V, V _{GS} = 0 V			- 1			
Zero Gate Voltage Drain Current		$V_{DS} = -8 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 70 ^{\circ}\text{C}$			- 5	μΑ		
On-State Drain Current ^a	I _{D(on)}	$V_{DS} = -5 \text{ V}, V_{GS} = -4.5 \text{ V}$	- 3			Α		
		V _{GS} = - 4.5 V, I _D = - 1 A		0.230	0.280			
Drain-Source On-State Resistance ^a	R _{DS(on)}	$V_{GS} = -2.5 \text{ V}, I_D = -0.5 \text{ A}$		0.315	0.380	Ω		
		V _{GS} = - 1.8 V, I _D = - 0.3 A		0.440	0.530			
Forward Transconductance ^a	9 _{fs}	V _{DS} = - 5 V, I _D = - 1 A		3.5		S		
Diode Forward Voltage ^a	V_{SD}	I _S = - 0.3 A, V _{GS} = 0 V			- 1.2	V		
Dynamic ^b								
Total Gate Charge	Q_g			2.6	4	nC		
Gate-Source Charge	Q_{gs}	$V_{DS} = -4 \text{ V}, V_{GS} = -4.5 \text{ V}, I_{D} = -1 \text{ A}$		0.6				
Gate-Drain Charge	Q_{gd}			0.5				
Turn-On Delay Time	t _{d(on)}			8	15			
Rise Time	t _r	V_{DD} = - 4 V, R_L = 4 Ω		55	80			
Turn-Off Delay Time	t _{d(off)}	$\text{I}_\text{D}\cong$ - 1 A, V_GEN = - 4.5 V, R_g = 6 Ω		17	25	ns		
Fall Time	t _f			12	20			
Source-Drain Reverse Recovery Time	t _{rr}	I _F = - 1 A, dI/dt = 100 A/μs		27	45			

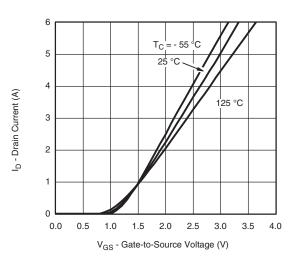
Notes:

- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

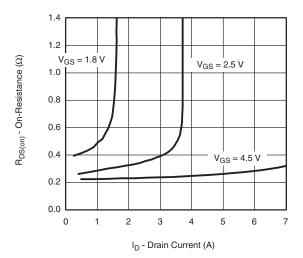




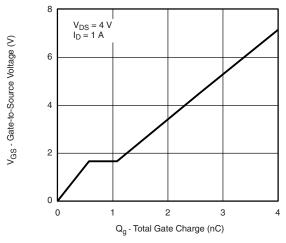
Transfer Characteristics



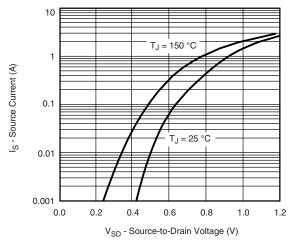
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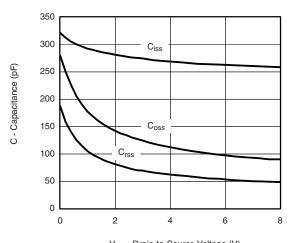
On-Resistance vs. Drain Current



Gate Charge

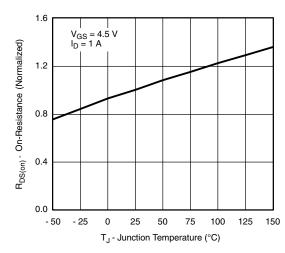


Source-Drain Diode Forward Voltage

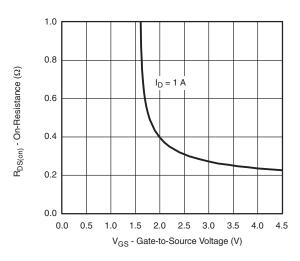


V_{DS} - Drain-to-Source Voltage (V)

Capacitance



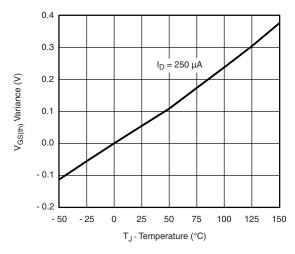
On-Resistance vs. Junction Temperature

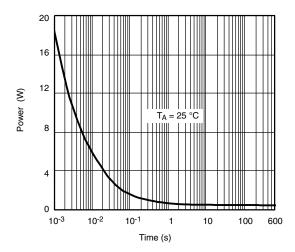


On-Resistance vs. Gate-to-Source Voltage

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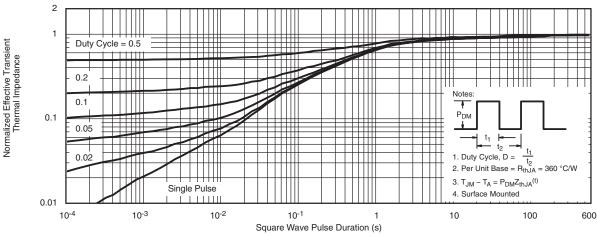
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



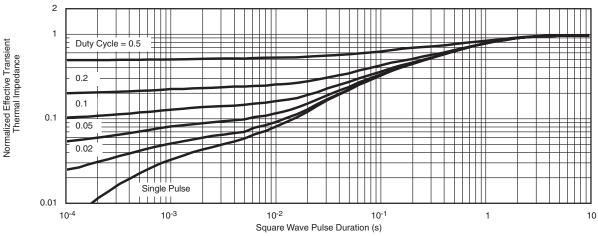


Threshold Voltage

Single Pulse Power



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot

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